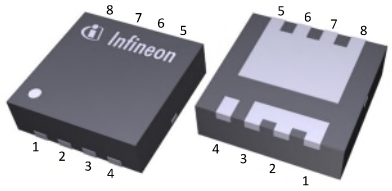
MOSFET

OptiMOS™5 Power-Transistor, 150 V

PG-TSDSON-8 FL



Features

- Ideal for high frequency switching and synchronous rectification
- Optimized technology for DC/DC converters
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC[1] for target applications
- Halogen-free according to IEC61249-2-21
- Higher solder joint reliability with enlarged source interconnection

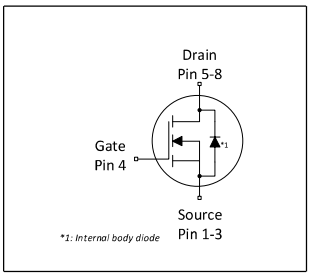


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	150	V
$R_{DS(on),max}$	30	mΩ
I_D	32	A
Q_{rr}	10.9	nC

Type / Ordering Code	Package	Marking	Related Links
BSZ300N15NS5	PG-TSDSON-8 FL	300N15N	-

[1] J-STD20 and JESD22

Table of Contents

1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	- -	- -	32 21	A	T_C=25 °C T_C=100 °C
Pulsed drain current[1]	$I_{D,pulse}$	-	-	128	A	T_C=25 °C
Avalanche energy, single pulse[2]	E_{AS}	-	-	30	mJ	I_D=20 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	62.5	W	T_C=25 °C
Operating and storage temperature	T_j, T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	1.2	2	K/W	-
Device on PCB, 6 cm^2 cooling area[3]	R_{thJA}	-	-	60	K/W	-

3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	150	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	3.0	3.8	4.6	V	V_{DS}=V_{GS}, I_D=32 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	1 100	µA	V_{DS}=120 V, V_{GS}=0 V, T_j=25 °C V_{DS}=120 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	1	100	nA	V_{GS}=20 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	25.5 28.1	30 49	mΩ	V_{GS}=10 V, I_D=16 A V_{GS}=8 V, I_D=8 A
Gate resistance[4]	R_G	0.4	0.8	1.2	Ω	-
Transconductance	g_{fs}	11	22	-	nC	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=16 A

[1] See Diagram 3 for more detailed information
[2] See Diagram 13 for more detailed information
[3] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm^2 (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.
[4] Defined by design. Not subject to production test

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance[1]	C_{iss}	-	730	950	pF	V_{GS}=0 V, V_{DS}=75 V, f=1 MHz
Output capacitance[1]	C_{oss}	-	180	230	pF	V_{GS}=0 V, V_{DS}=75 V, f=1 MHz
Reverse transfer capacitance[1]	C_{rss}	-	6	11	pF	V_{GS}=0 V, V_{DS}=75 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	7.0	-	ns	V_{DD}=75 V, V_{GS}=10 V, I_D=16 A, $R_{G,ext}$=3 Ω
Rise time	t_r	-	2.2	-	ns	V_{DD}=75 V, V_{GS}=10 V, I_D=16 A, $R_{G,ext}$=3 Ω
Turn-off delay time	$t_{d(off)}$	-	7.5	-	ns	V_{DD}=75 V, V_{GS}=10 V, I_D=16 A, $R_{G,ext}$=3 Ω
Fall time	t_f	-	2.2	-	ns	V_{DD}=75 V, V_{GS}=10 V, I_D=16 A, $R_{G,ext}$=3 Ω

Table 6 Gate charge characteristics[2]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	4.3	-	nC	V_{DD}=75 V, I_D=16 A, V_{GS}=0 to 10 V
Gate to drain charge[1]	Q_{gd}	-	2.2	3.4	nC	V_{DD}=75 V, I_D=16 A, V_{GS}=0 to 10 V
Switching charge	Q_{sw}	-	4.5	-	nC	V_{DD}=75 V, I_D=16 A, V_{GS}=0 to 10 V
Gate charge total[1]	Q_g	-	10.1	13	nC	V_{DD}=75 V, I_D=16 A, V_{GS}=0 to 10 V
Gate plateau voltage	$V_{plateau}$	-	5.9	-	V	V_{DD}=75 V, I_D=16 A, V_{GS}=0 to 10 V
Output charge[1]	Q_{oss}	-	28	37	nC	V_{DD}=75 V, V_{GS}=0 V

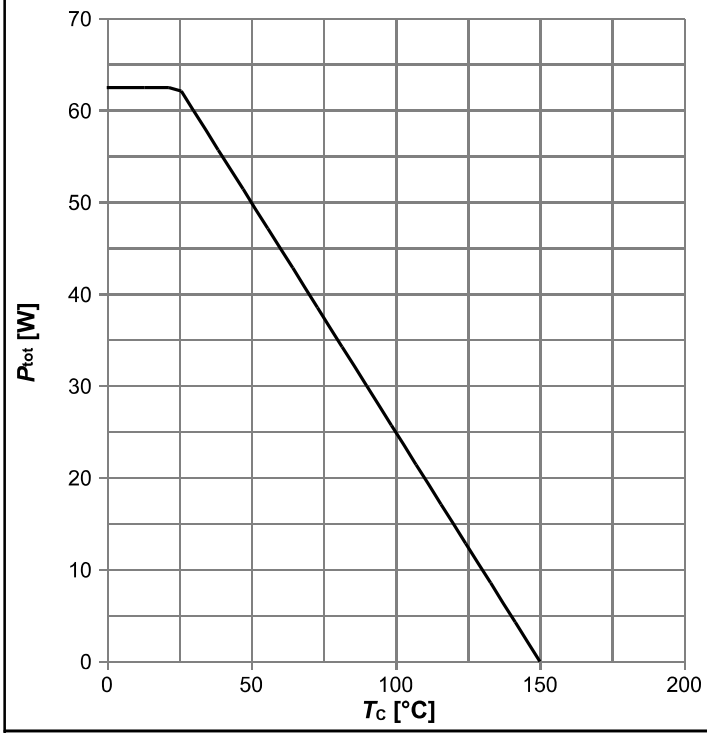
Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continous forward current	I_S	-	-	32	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	128	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	0.88	1.2	V	V_{GS}=0 V, I_F=16 A, T_j=25 °C
Reverse recovery time[1]	t_{rr}	-	20.5	41	ns	V_R=75 V, I_F=*16*, di_F/dt=100 A/µs
Reverse recovery charge[1]	Q_{rr}	-	10.9	21.8	nC	V_R=75 V, I_F=*16*, di_F/dt=100 A/µs

[1] Defined by design. Not subject to production test
[2] See "Gate charge waveforms" for parameter definition

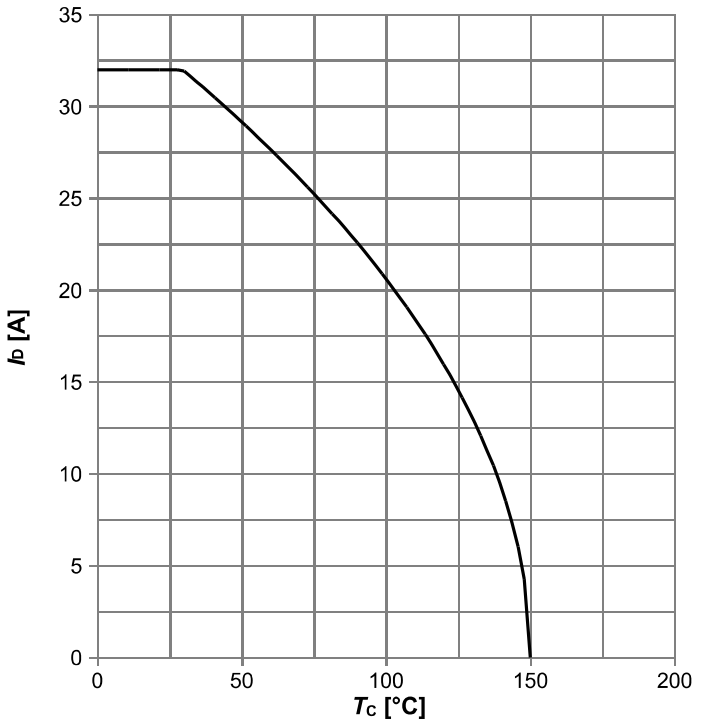
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



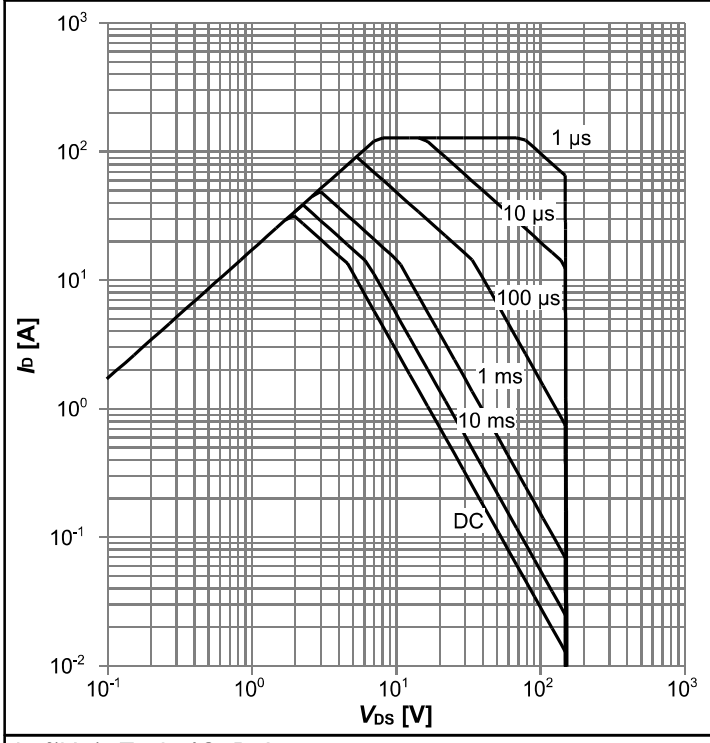
$P_{tot}=f(T_C)$

Diagram 2: Drain current



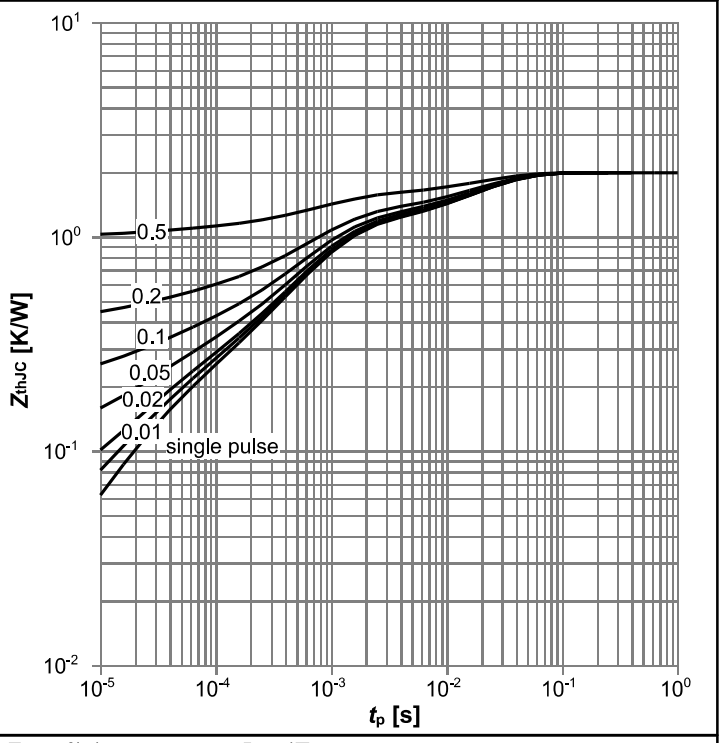
$I_D=f(T_C)$; $V_{GS}\geq 10$ V

Diagram 3: Safe operating area



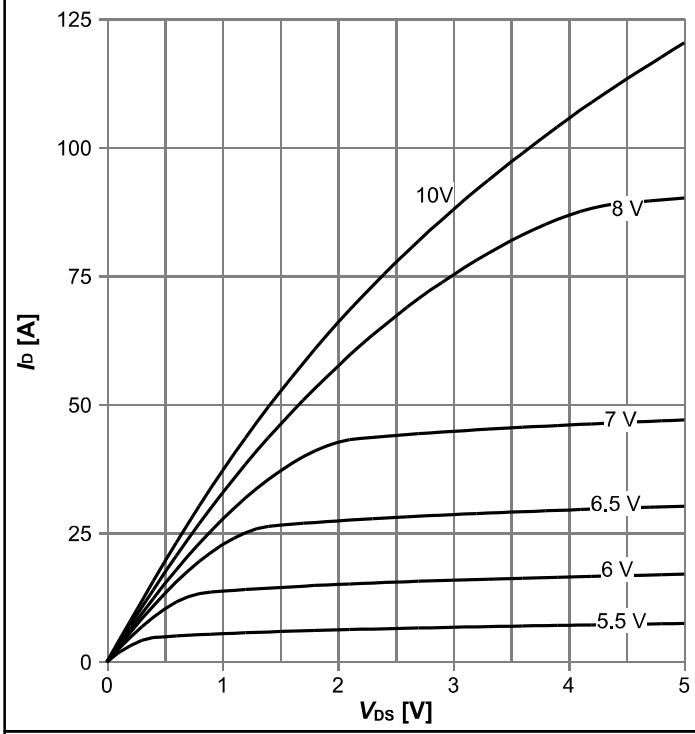
$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

Diagram 4: Max. transient thermal impedance



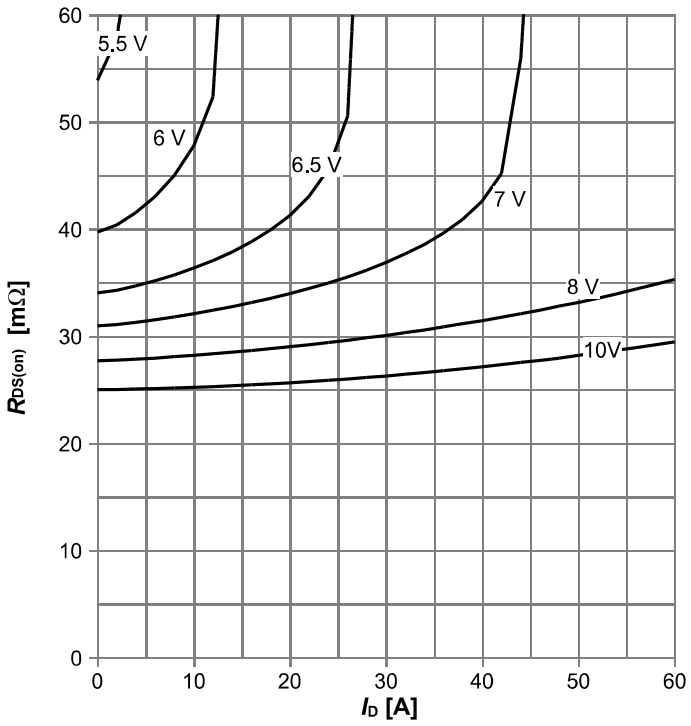
$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



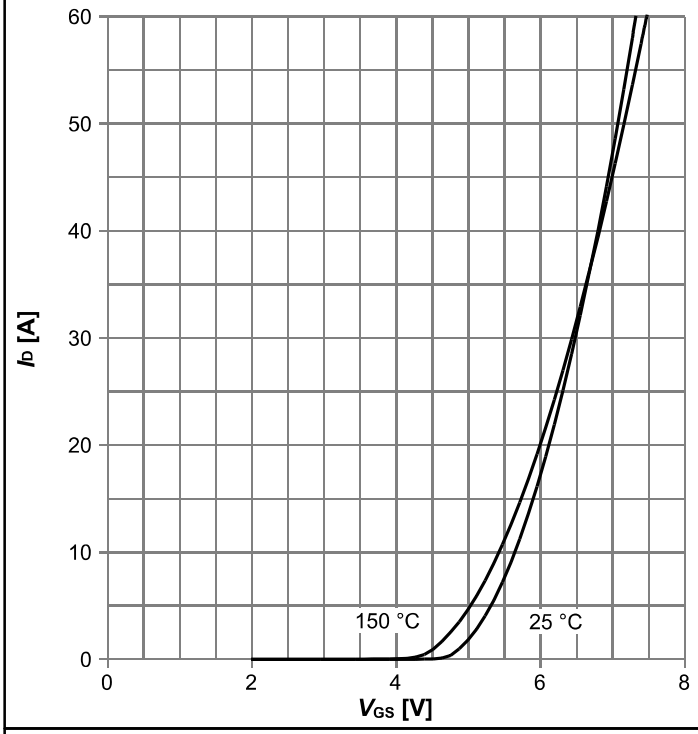
$I_D=f(V_{DS})$; $T_j=25$ °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



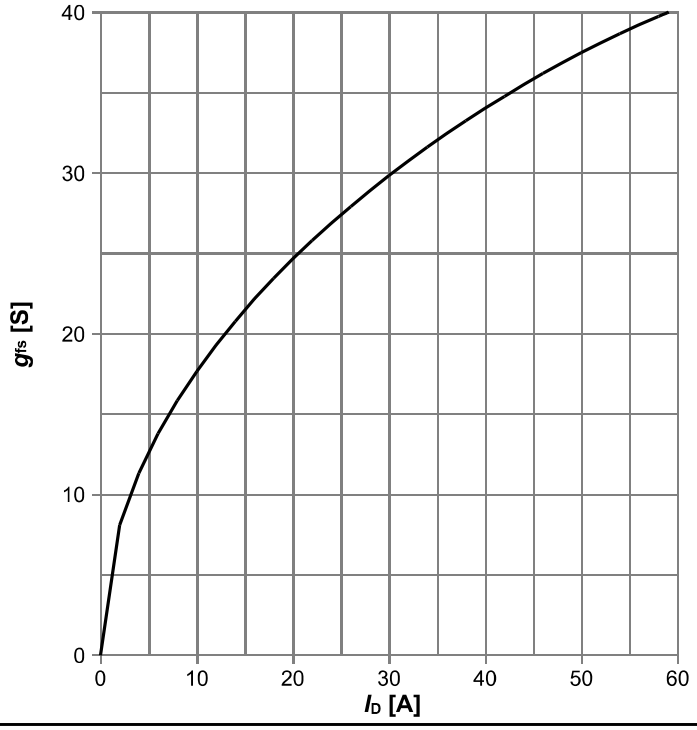
$R_{DS(on)}=f(I_D)$; $T_j=25$ °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



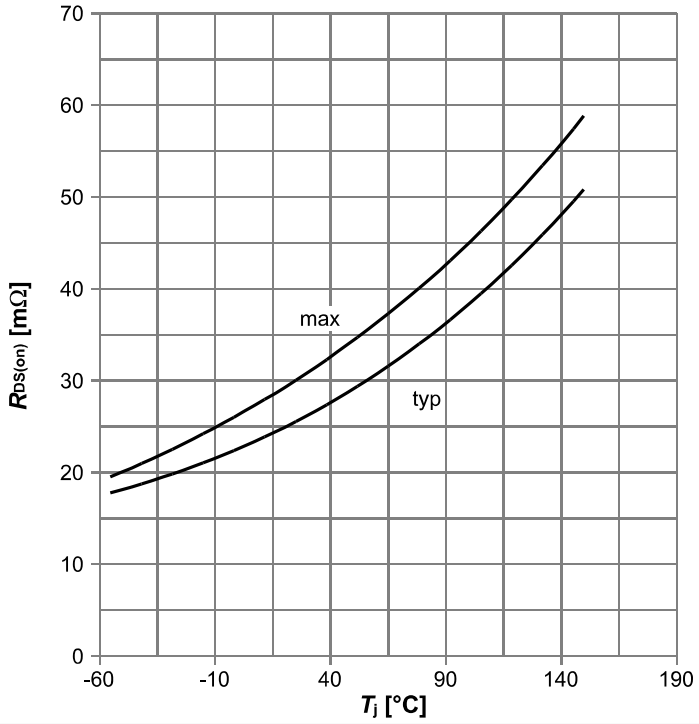
$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



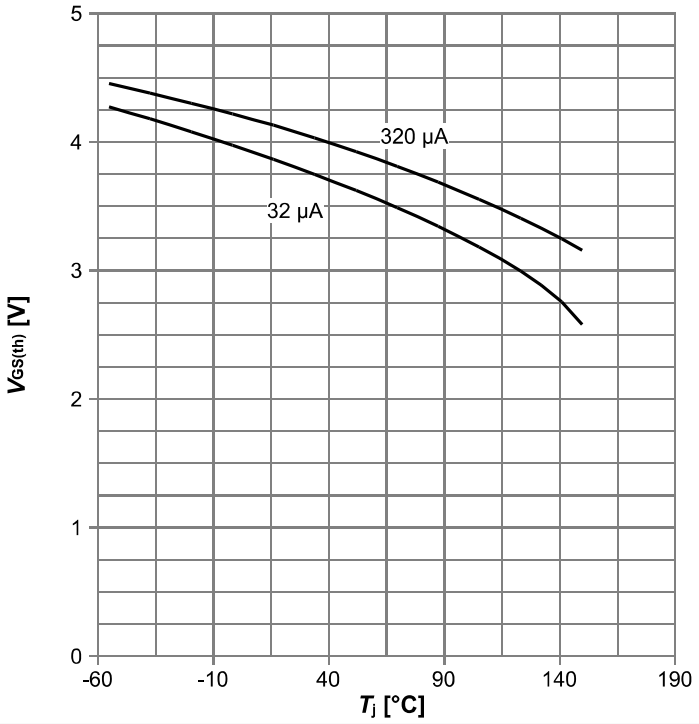
$g_{fs}=f(I_D)$; $T_j=25$ °C

Diagram 9: Drain-source on-state resistance



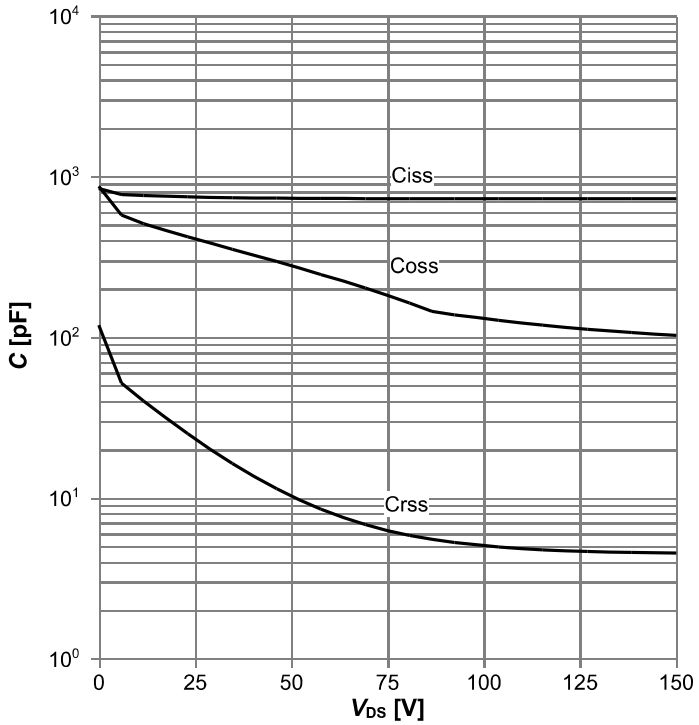
$R_{DS(on)}$=f(T_j); I_D=16 A; V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



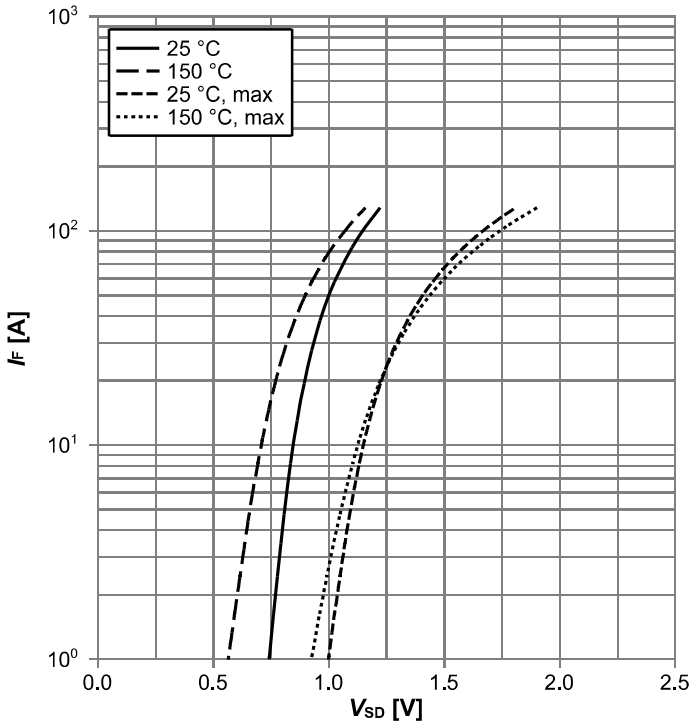
$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



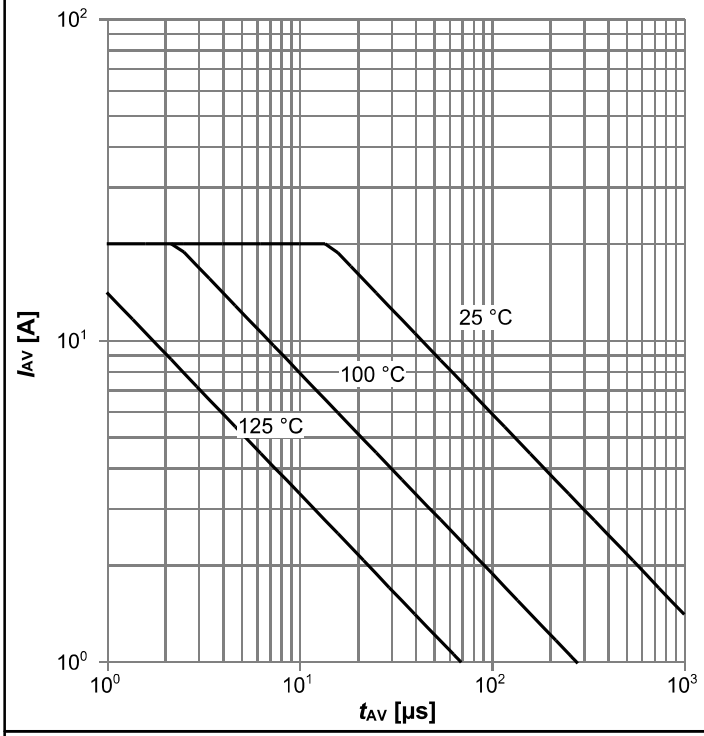
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



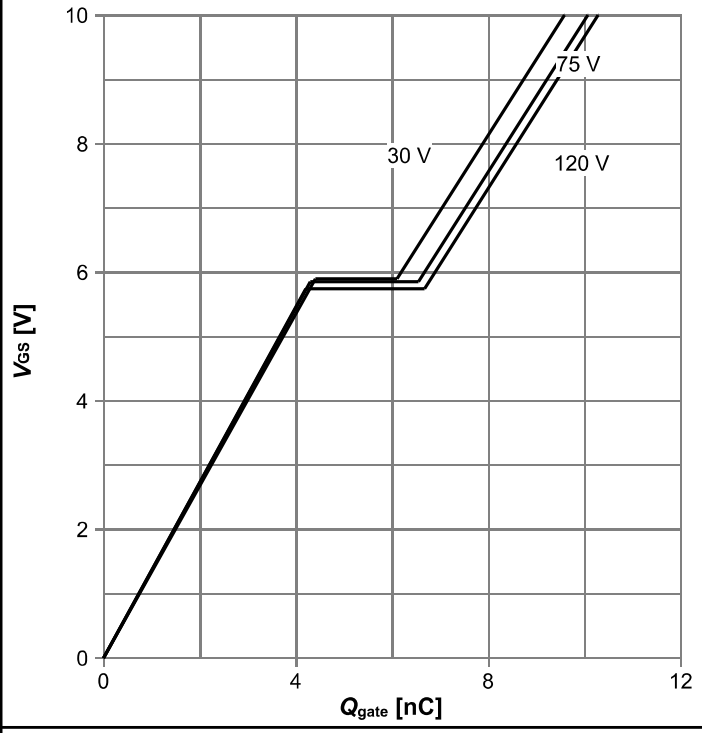
I_F=f(V_{SD}); parameter: T_j

Diagram 13: Avalanche characteristics



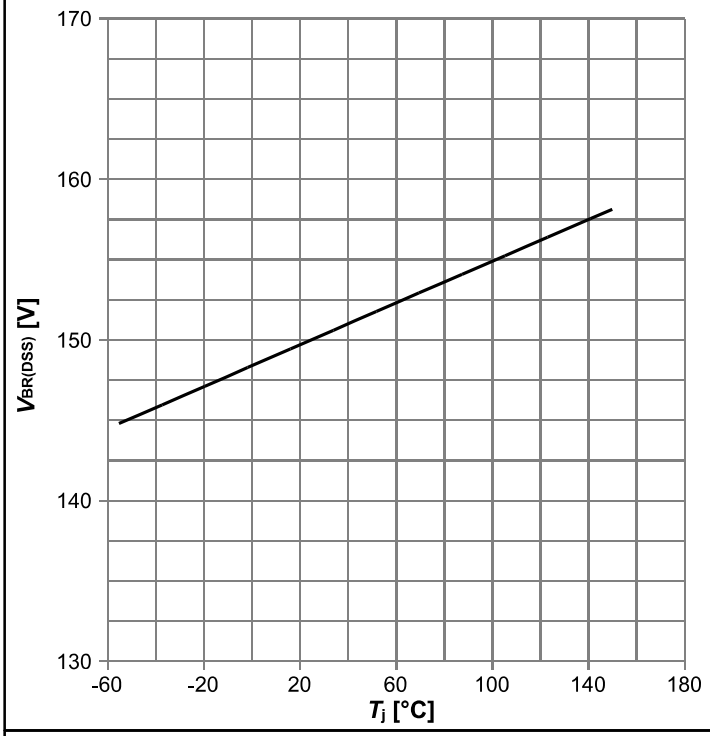
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



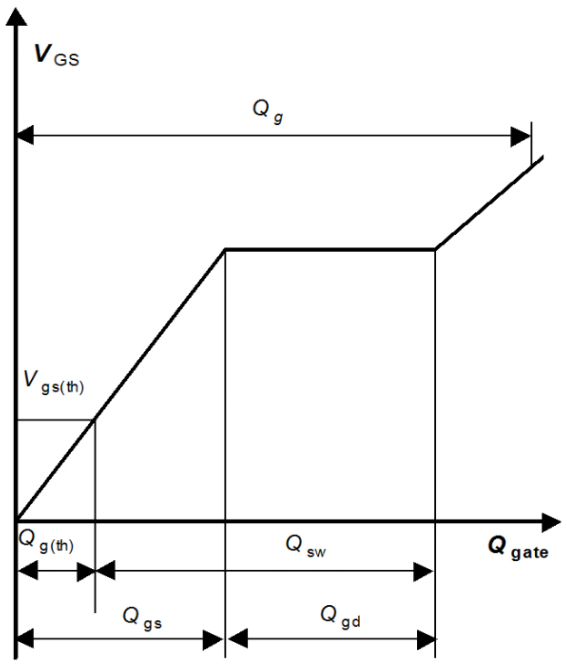
$V_{GS}=f(Q_{gate})$; $I_D=16$ A pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

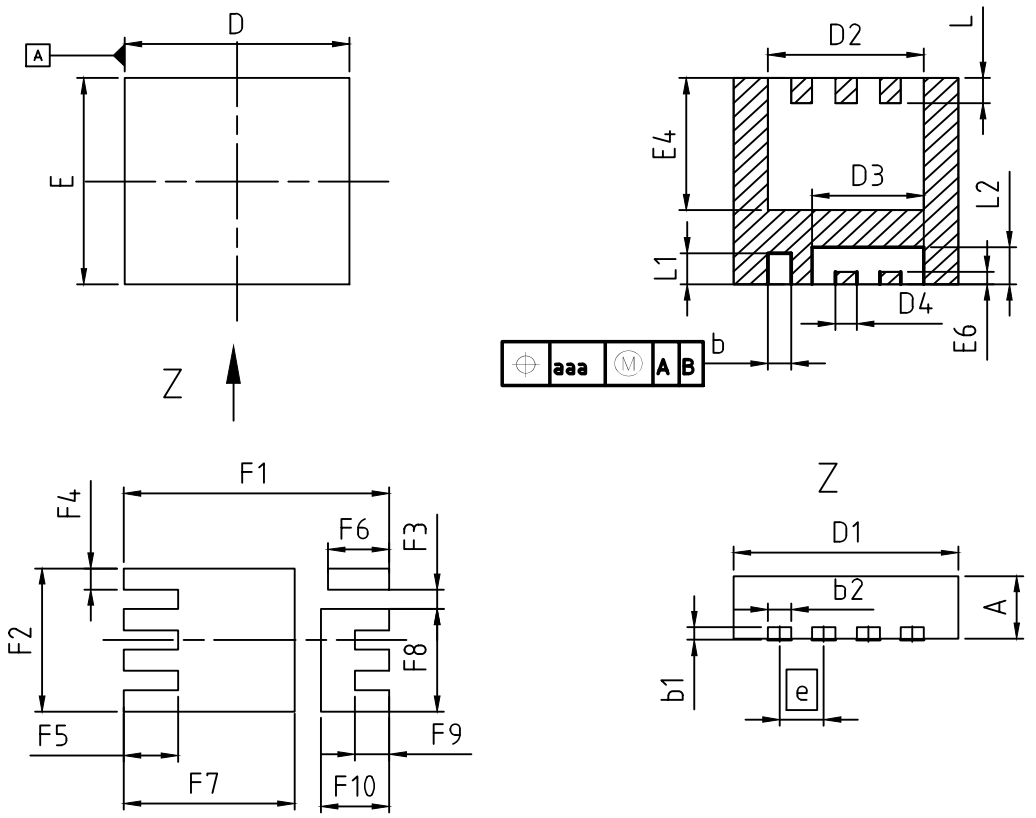


$V_{BR(DSS)}=f(T_j)$; $I_D=1$ mA

Diagram Gate charge waveforms



5 Package Outlines



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
b	0.24	0.44	0.009	0.017
b1	0.10	0.30	0.004	0.012
b2	0.24	0.44	0.009	0.017
D=D1	3.20	3.40	0.126	0.134
D2	2.19	2.39	0.086	0.094
D3	1.54	1.74	0.061	0.069
D4	0.21	0.41	0.008	0.016
E	3.20	3.40	0.126	0.134
E4	2.01	2.21	0.079	0.087
E6	0.10	0.30	0.004	0.012
e	0.65 (BSC)		0.026 (BSC)	
N	8		8	
L	0.30	0.51	0.012	0.020
L1	0.40	0.70	0.016	0.028
L2	0.50	0.70	0.020	0.028
aaa	0.25		0.010	
F1	3.90		0.154	
F2	2.29		0.090	
F3	0.31		0.012	
F4	0.34		0.013	
F5	0.80		0.031	
F6	1.00		0.039	
F7	2.51		0.099	
F8	1.64		0.065	
F9	0.50		0.020	

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SCALE
0 2.5 5mm

EUROPEAN PROJECTION

ISSUE DATE
27-12-2010

REVISION
02

Figure 1 Outline PG-TSDSON-8 FL, dimensions in mm/inches

Revision History

BSZ300N15NS5

Revision: 2021-06-09, Rev. 2.2

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2015-05-27	Release of final version
2.1	2015-06-09	Update avalanche energy
2.2	2021-06-09	Update "Marking"

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